

## Всички цитати

- **Звено: ( ЦЛПФ ) Централна лаборатория по приложна физика - Пловдив**
- **Година: 2016 ÷ 2016**
- **Тип записи: Всички записи**

Брой цитирани публикации: 8

Брой цитиращи източници: 22

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2. Omotoso, E., Meyer, W.E., Coelho, S.M.M., Diale, M., Ngoepe, P.N.M., Auret, F.D., "Electrical characterization of defects introduced during electron beam deposition of W Schottky contacts on n-type 4H-SiC", Materials Science in Semiconductor Processing, Volume 51, 15 August 2016, Pages 20-24, @2016
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8. Kuchuk, A.V., Borowicz, P., Wzorek, M., Borysiewicz, M., Ratajczak, R., Golaszewska, K., Kaminska, E., Kladko, V., Piotrowska, A., "Ni-Based Ohmic Contacts to n-Type 4H-SiC: The Formation Mechanism and Thermal Stability", Advances in Condensed Matter Physics, Volume 2016, 2016, Article number

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16. С. О. Иванчиков, З. А. Никонова, О. Ю. Небеснюк, М. Салам Алайк, Исследование основных закономерностей дефектообразования при получении эпитаксиальных композиций и контактных систем для фотэлектрических преобразователей, Новые Материалы и Нанотехнологии, 2016, 2, 9-13, УДК 621.315.592, @2016

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